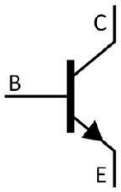
WR0<50P ḾḾÞ QSQ ÆḾчs ‖ ㄱ Silicon NPN transistor in a TO-92LM Plastic Package.

ت ᄃ я ∪ Ң ı ль 5VE4576 Й ´

Low $V_{CE(sat)}$,complementary pair with 2SB1243.

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General power amplifier applications.

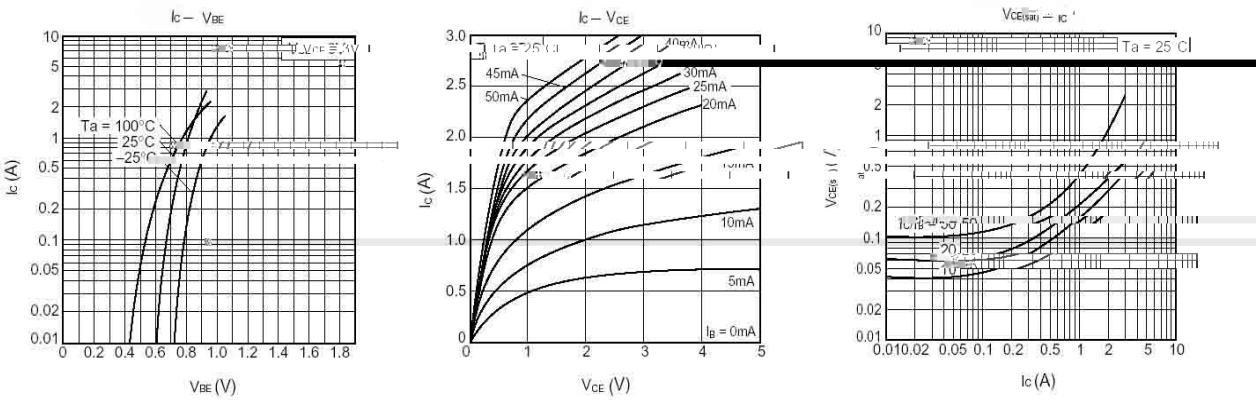


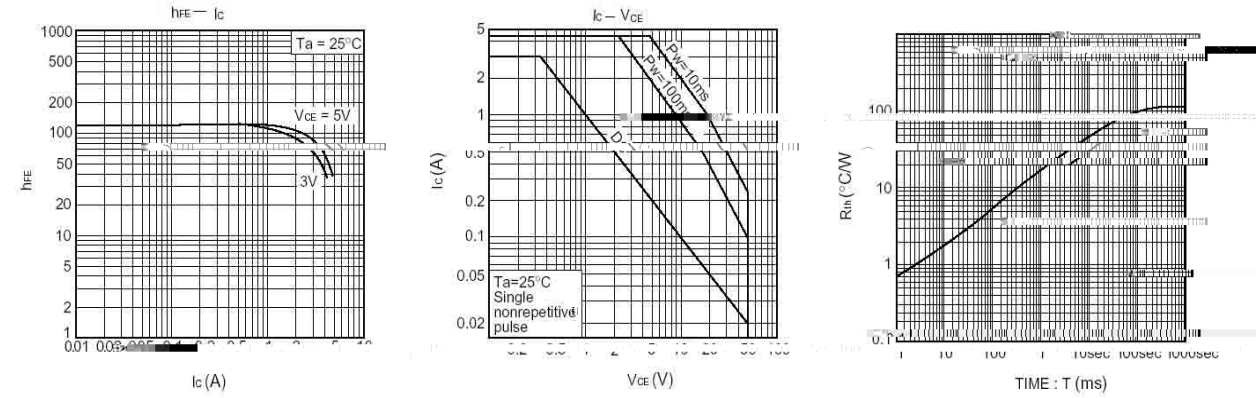


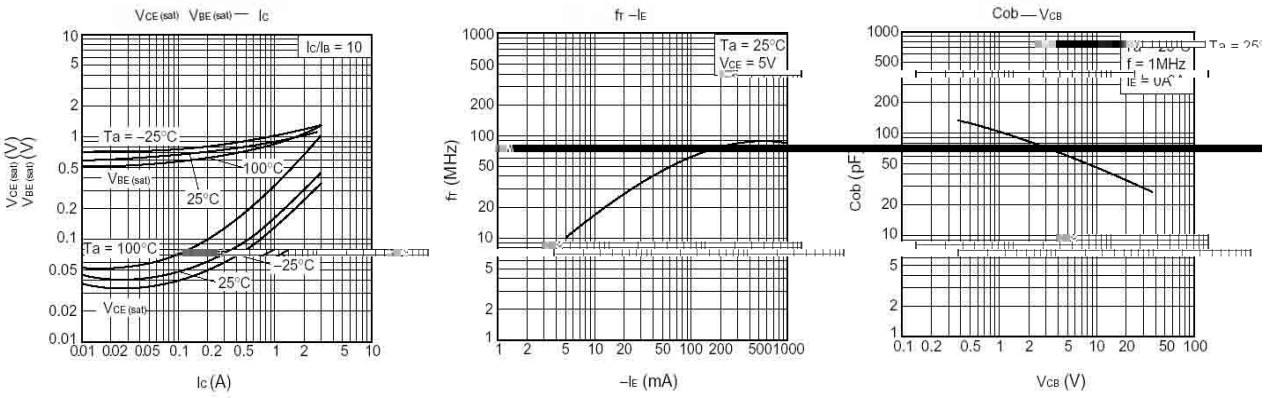
PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	82 180	120 270	180 390

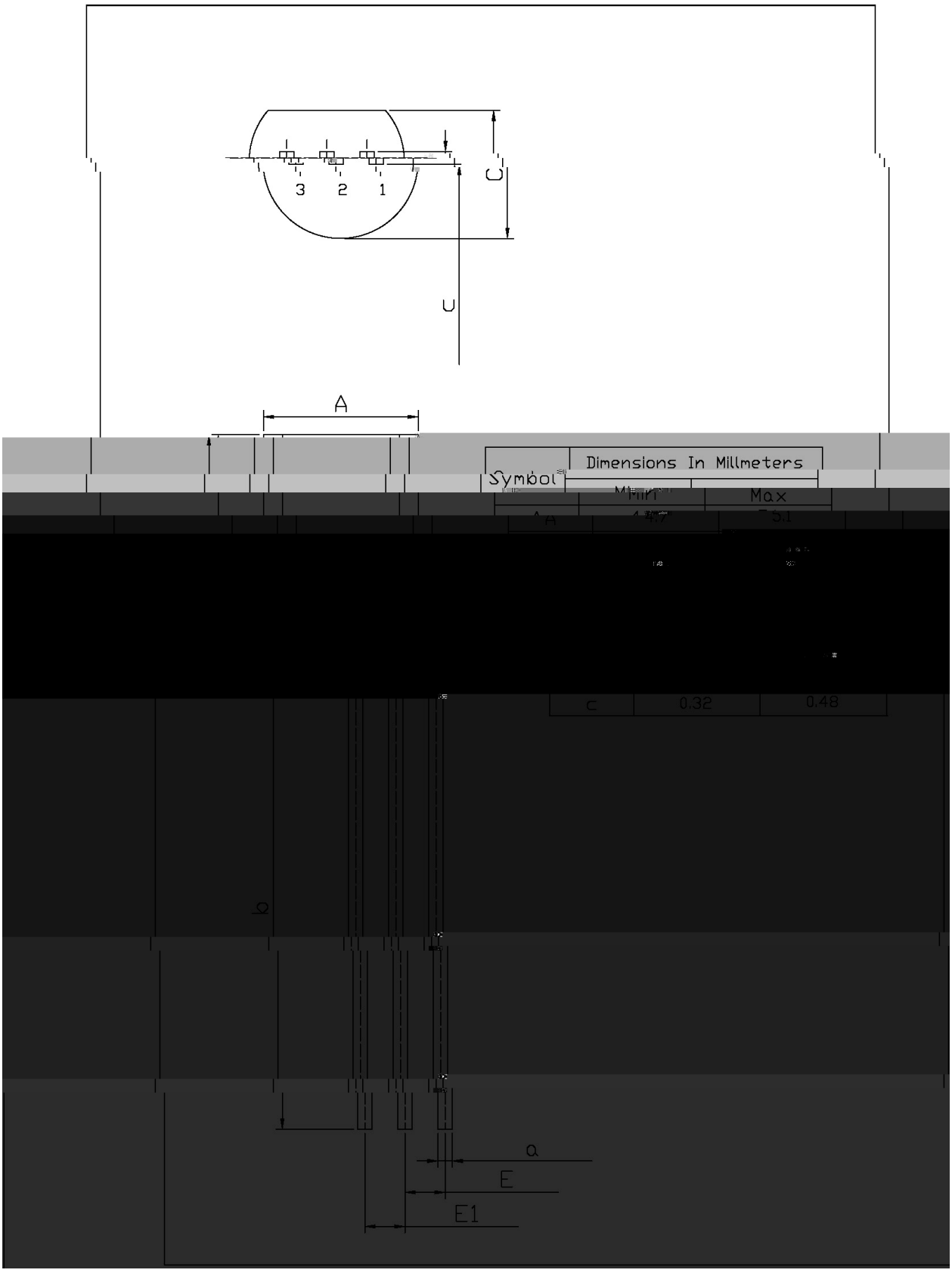
v ‴Ω Parameter	ϒ N Symbol	‴Ω Ö Rating	D Ђ Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	3.0	A
Collector Current (Pulse)	I_{CP}	4.5	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55	

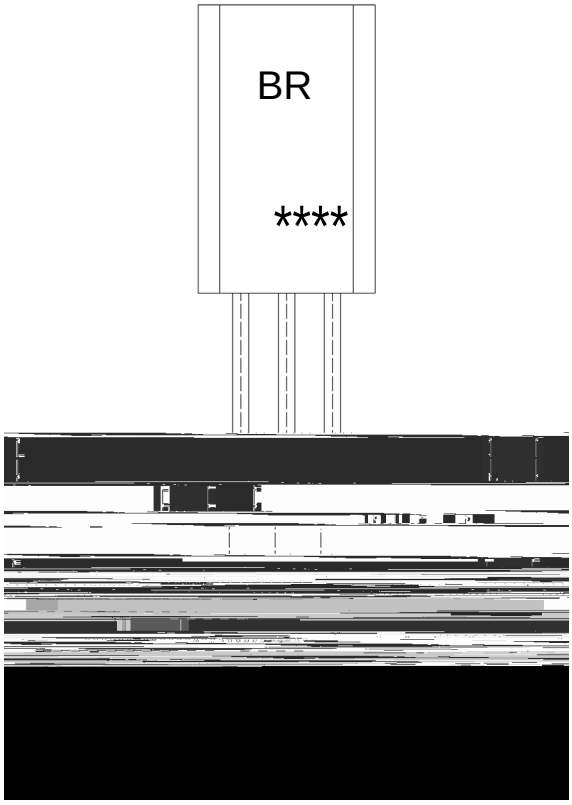

Ic – VBE
Ta = 100°C
25°C
–25°C
Ic (A)
VBE (V)
Ic – VCE
45mA
50mA
30mA
25mA
20mA
10mA
5mA
IB = 0mA
Ic (A)
VCE (V)
VCE(sat) – Ic
Ta = 25°C
Ic (A)


hFE – Ic
Ta = 25°C
VCE = 5V
3V
hFE
Ic (A)
Ic – VCE
Pw=10ms
Pw=100ms
D
Ta=25°C
Single
nonrepetitive
pulse
Ic (A)
VCE (V)
TIME : T (ms)


VCE(sat) VBE(sat) – Ic
Ic/IB = 10
Ta = –25°C
100°C
VBE(sat)
25°C
Ta = 100°C
–25°C
25°C
VCE(sat)
Ic (A)
fT –IE
Ta = 25°C
VCE = 5V
fT (MHz)
–IE (mA)
Cob – VCB
f = 1MHz
Cob (pF)
VCB (V)

TO-92LM Unit: mm





ب ˝ χ	
EU=	ѭ ҙ и Ґ
G4 ; 97 χ	ѭ ҙ N Ґ
S=	ѭ k ıн ‘ 6 Ґ
---- χ	ѭ ı ғ ӈ̈ N Ґ ı ₰ ı ғ ӈ̈ N Ψ ק

Note:

BR:	Company Code.
D1864:	Product Type.
P:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı `H ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ł ı `H ڑ `Y ٨ ʁ 5 ° 0.5sec;

3 ì ˙ ٩ ˛ ɔ ѡ ỷ ʁ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:255 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

□ ỷ χ 270 ° 5 ł `H ڑ χ 10 ° 1 sec. Temp.:270±5